

PNP SILICON AMPLIFIER TRANSISTOR

Qualified per MIL-PRF-19500/357

Devices

2N3634	2N3635	2N3636	2N3637
2N3634L	2N3635L	2N3636L	2N3637L

Qualified Level

JAN
JANTX
JANTXV
JANS

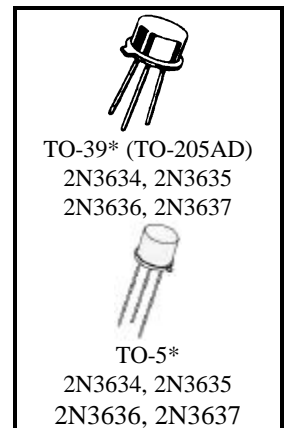
MAXIMUM RATINGS

Ratings	Symbol	2N3634* 2N3635*	2N3636* 2N3637*	Unit
Collector-Emitter Voltage	V_{CEO}	140	175	Vdc
Collector-Base Voltage	V_{CBO}	140	175	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current	I_C	1.0		Adc
Total Power Dissipation	P_T	@ $T_A = +25^{\circ}C^{(1)}$	1.0	W
		@ $T_C = +25^{\circ}C^{(2)}$	5.0	W
Operating & Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200		$^{\circ}C$

*Electrical characteristics for "L" suffix devices are identical to the "non L" corresponding devices

1) Derate linearly 5.71 mW/ $^{\circ}C$ for $T_A > +25^{\circ}C$

2) Derate linearly 28.6 mW/ $^{\circ}C$ for $T_C > +25^{\circ}C$



*See appendix A for package outline

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Current $I_C = 10$ mAdc	2N3634, 2N3635 2N3636, 2N3637	$V_{(BR)CEO}$	140 175	Vdc
Collector-Base Cutoff Current $V_{CB} = 100$ Vdc $V_{CB} = 140$ Vdc	2N3634, 2N3635	I_{CBO}	100 10	η Adc μ Adc
Emitter-Base Cutoff Current $V_{EB} = 3.0$ Vdc $V_{EB} = 5.0$ Vdc		I_{EBO}	50 10	η Adc μ Adc
Collector-Emitter Cutoff Current $V_{CE} = 100$ Vdc		I_{CEO}	10	μ Adc

